PhotonHub Demo Centre Thick-SOI photonics for sensing and imaging

Course Provider VTT Technical Research Centre of Finland Ltd., Finland



European Photonics Innovation Academy

Course Overview

<u>Photonic integrated circuits (PICs)</u> can be realized on many different technology platforms and used for numerous different applications. This course focuses on the so-called <u>Thick-SOI platform and its use for sensing and imaging</u> <u>applications in the near and mid-infrared region</u>. Primary focus is on 3 µm thick silicon-on-insulator (SOI) waveguide technology, which is the most mature PIC technology platform at VTT. This platform is also available for small-to-medium volume contract manufacturing via VTT, and there is path to large-volume manufacturing via VTT's partners. Process design kits are available in multiple PIC design software platforms.

This one-day hands-on training course provides <u>industry</u> an overview of the Thick-SOI PIC platform and its feasibility in sensing and imaging applications. A <u>clean room tour</u> in Micronova offers an overview of the used fabrication methods and facilities. Hands-on training includes <u>1) the design of 3 µm SOI PICs using PIC design</u> <u>software, 2) General cleanroom visit and introduction to state-of-the-art manufacturing tools, and 3) PIC testing in the photonics measurement lab</u>. The last part includes semi-automated fiber-to-waveguide alignment, optical beam steering with an optical phased array (OPA) and testing of other silicon photonic chips.



Target Audience

It is desirable but not essential that course attendees have a basic understanding of photonics. The course is ideally suited to those planning to develop new photonic products based on low-loss photonic integrated circuits (PICs) operating within the 1.2-6 µm wavelength range where the thick (µm-scale) silicon-on-insulator (SOI) waveguides can operate.

Expected Outcomes

1) Understanding the technical advantages and limitations of Thick-SOI PIC technology, as well as its key applications

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- 2) Learn how the Thick-SOI PICs are designed & simulated (hands-on activity)
- 3) See the fabrication process of 3 µm SOI PICs (visit to the clean room)
- 4) Learn how the Thick-SOI PICs are tested at chip-level (hands-on activity)
- 5) See demonstrations of 3 µm SOI PICs in imaging applications (hands-on activity)



Version 6, 2023

3 µm

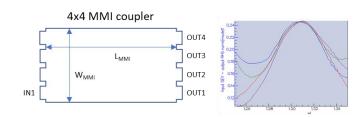
Course Schedule

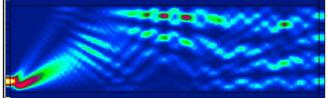
Time	Demo Activity
09:00 - 10:45	Introduction to the course, to Thick-SOI technology and its main applications
11:00 – 12:30	Demo 1: Design of 3 µm SOI PICs using a process design kit (hands-on)
13:30 – 15:00	Demo 2: Clean-room visit to see fabrication flow (hands-on)
15:15 – 17:00	Demo 3: Chip-level testing and demonstration of Thick-SOI in sensing & imaging (hands-on)
17:00 – 17:30	Follow-Up Questions & Close



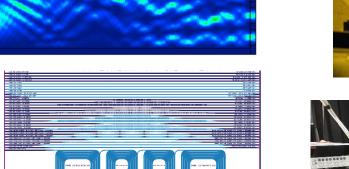
Course Trainers



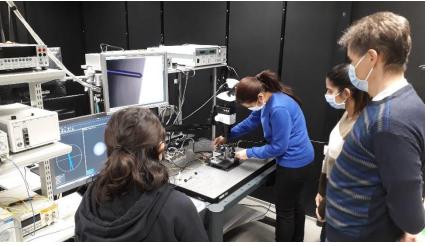












Course Director: Timo Aalto Course Manager: Somnath Paul

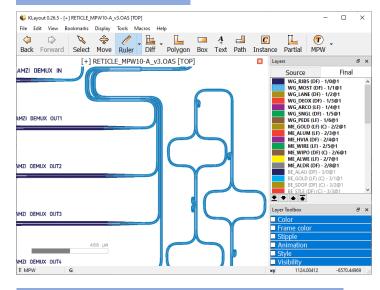
- Demo 1: Mikko Harjanne (PIC design)
- Demo 2: Fei Sun (clean room visit)
- Demo 3: Yisbel Marin / Somnath Paul (chip-level testing and application demos)



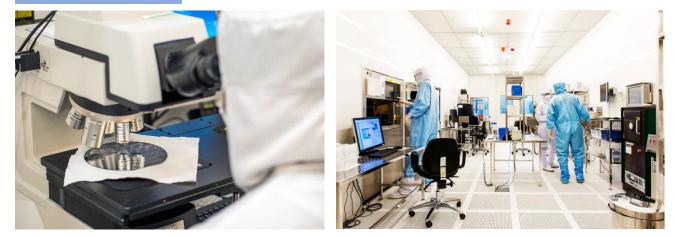
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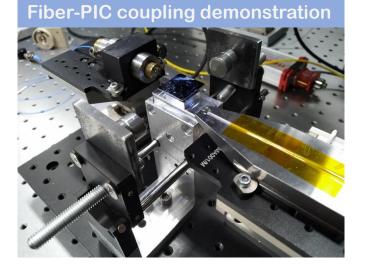
Course Demonstrators

PIC design demo



Clean room tour









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Course Location, Schedule & Cost



- Course location: VTT, Micronova, Tietotie 3, Espoo, Finland (few metro stops from downtown Helsinki)
- Course Schedule: 10.01.2024 (other dates to be confirmed later)
- Number of people: Maximum 10 people per course
- Course Cost: 250 Euros per person, includes catering and project consumables

Further Information

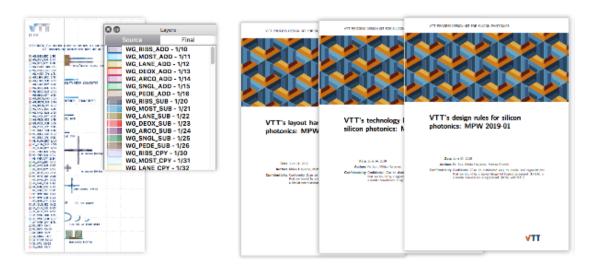
- timo.aalto@vtt.fi
- https://www.vttresearch.com/en
- www.photonhub.eu/euphotonicsacademy



Course Material (technical hand-outs)

Digital course materials:

- Course instructions and notes
- Copies of slides
- Video recordings
- Process design kit (PDK) for 3 µm SOI PICs (some parts require a signed design kit license agreement)



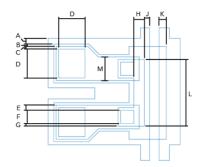


Figure 4.3: Mask parameters for the implanted heater.

Table 4.1: Parameter values related to Fig. 4.3.							
Dimension	Description	Mask layer	Min.	Typical	Unit		
А	Gap between wire and SOI sidewall	ME_WIRE	5.0	5.0	um		
в	Distance between pedestal edge and metal	WG_PEDE	1.0		um		
С	Gap between contact pad opening and metal edge	ME_WIP0	3.0	10.0	um		
D	Size of contact pad opening	ME_WIP0	60	100.0	um		
Е	Heater via to wire edge distance	ME_HVIA	3.0	3.0	um		
F	Size of heater via opening	ME_HVIA	5.0	5.0	um		
G	Heater via to implantation edge distance	NE_HVIA	1.0	1.0	um		
н	Implanted heater width	NP_PINP	3.0	4.0	um		
J	Gap between implantation edge and waveguide	NP_PINP	2.0	2.0	um		
к	Pedestal extension past waveguide edge	WG_PEDE	2.0		um		
L	Implanted heater length	NP_PINP		100.0	um		
м	Width of aluminium wire	ME_WIRE	5.0	7.0	um		



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Integrated Photonics, PIC, PIC Design, PDK, Silicon-on-Insulator, SOI, Wafer Processing, Sensing, Imaging, Optical Phased Array, Optical Fiber, Laser, Testing, Test automation

Relevant Technology & Application Domain

Technology: Silicon photonics

Application: Relevant to all application domains, but course focuses on sensing and imaging

